## TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

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#### ULTRA HIGH SPEED SWITCHING APPLICATION.

Low Forward Voltage  $: V_{F(3)} = 0.9V \text{ (Typ.)}$ 

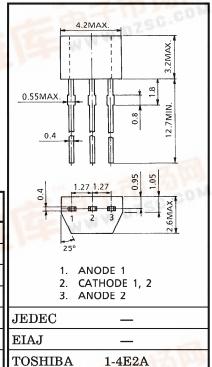
Fast Reverse Recovery Time: trr=1.6ns (Typ.)

Small Total Capacitance  $: C_T = 0.9pF (Typ.)$ WWW.DZSC

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	SYMBOL RATING	
Maximum (Peak) Reverse Voltage	$v_{RM}$	85	V
Reverse Voltage	$V_{\mathbf{R}}$	80	V
Maximum (Peak) Forward Current	$I_{FM}$	300 (*)	mA
Average Forward Current	IO	100 (*)	mA
Surge Current (10ms)	$I_{FSM}$	2 (*)	A
Power Dissipation	P	200	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm



WWW.DZSC.CO Weight: 0.13g

(\*) Unit Rating. Total Rating = Unit Rating × 1.5.

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V <sub>F (1)</sub>	$I_{\mathbf{F}} = 1 \text{mA}$	_	0.60	_	V
$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.72		
$V_{\mathrm{F}(3)}$	$I_{ m F}$ = 100mA	-	0.90	1.20	
I <sub>R (1)</sub>	$V_R=30V$	-		0.1	$\mu$ <b>A</b>
I <sub>R (2)</sub>	$V_R = 80V$		WAY.	0.5	
$\mathbf{C}_{\mathbf{T}}$	$V_R=0$ , $f=1MHz$		0.9	3.0	рF
trr	I <sub>F</sub> =10mA (Fig.1)		1.6	4.0	ns
EJIN DZS	C.COM				
	V <sub>F</sub> (1) V <sub>F</sub> (2) V <sub>F</sub> (3) I <sub>R</sub> (1) I <sub>R</sub> (2) C <sub>T</sub>	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

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TOSHIBA 155201

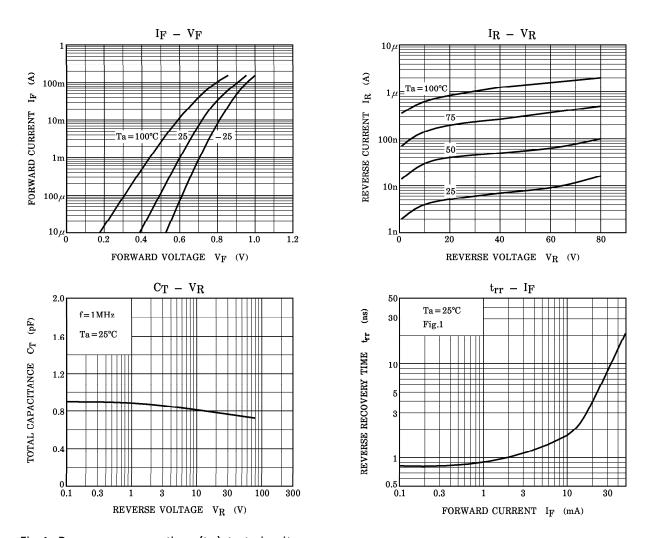


Fig.1 Reverse recovery time (t<sub>rr</sub>) test circuit

